

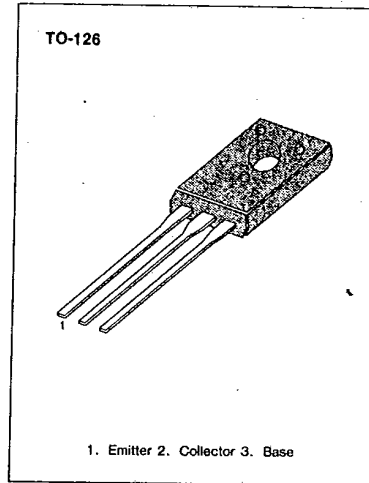
MJE210

PNP EPITAXIAL SILICON TRANSISTOR

COLLECTOR-EMITTER SUSTAINING VOLTAGE
 LOW COLLECTOR-EMITTER
 SATURATION VOLTAGE
 HIGH CURRENT GAIN-BANDWIDTH
 PRODUCT-MIN $f_T=65\text{MHz}$ @ $I_C=-100\text{mA}$

Complementary to MJE200

T-33-17



3

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-40	V
Collector-Emitter Voltage	V_{CE0}	-25	V
Emitter-Base Voltage	V_{EB0}	-8	V
Collector Current	I_C	-5	A
Collector Dissipation	P_C	15	W
Junction Temperature	T_J	-150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CE0(SUS)}$	$I_C=-10\text{mA}, I_B=0$	-25		V
Collector Cutoff Current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$		-100	nA
Emitter Cutoff Current	I_{EBO}	$V_{CB}=-40\text{V}, I_E=0, T_J=125^\circ\text{C}$		-100	μA
DC Current Gain	h_{FE}	$V_{BE}=-8\text{V}, I_C=0$		-100	nA
		$V_{CE}=-1\text{V}, I_C=-500\text{mA}$	70		
		$V_{CE}=-1\text{V}, I_C=-2\text{A}$	45	180	
		$V_{CE}=-2\text{V}, I_C=-5\text{A}$	10		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$		-0.3	V
		$I_C=-2\text{A}, I_B=-200\text{mA}$		-0.75	V
		$I_C=-5\text{A}, I_B=-1\text{A}$		-1.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-5\text{A}, I_B=-1\text{A}$		-2.5	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=-1\text{V}, I_C=-2\text{A}$		-1.6	V
Current Gain-Bandwidth Product	f_T	$V_{CE}=-10\text{V}, I_C=-100\text{mA}$ $f=10\text{MHz}$	65		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=0.1\text{MHz}$		120	pF

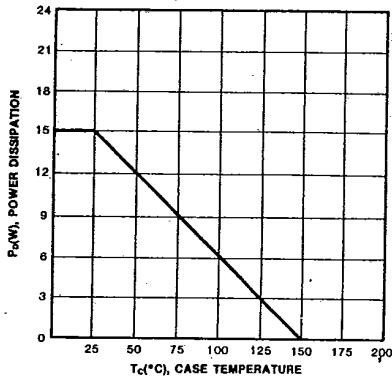


MJE210

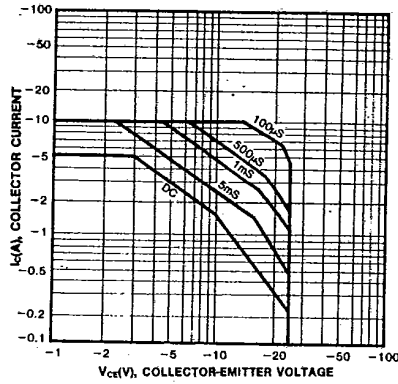
PNP EPITAXIAL SILICON TRANSISTOR

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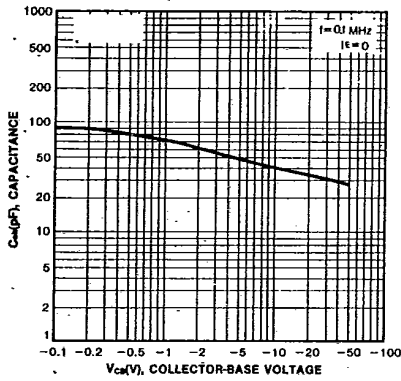
POWER DERATING



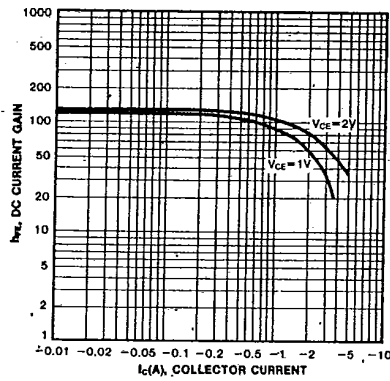
FORWARD BIAS SAFE OPERATING AREA



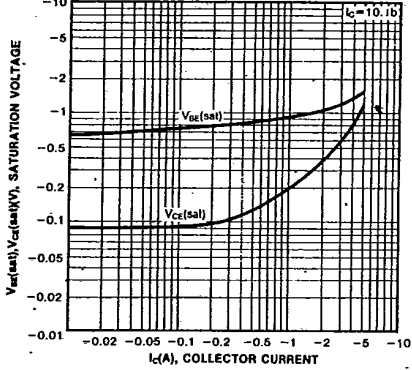
COLLECTOR OUTPUT CAPACITANCE



DC CURRENT GAIN



COLLECTOR-EMITTER SATURATION VOLTAGE
BASE-EMITTER SATURATION VOLTAGE

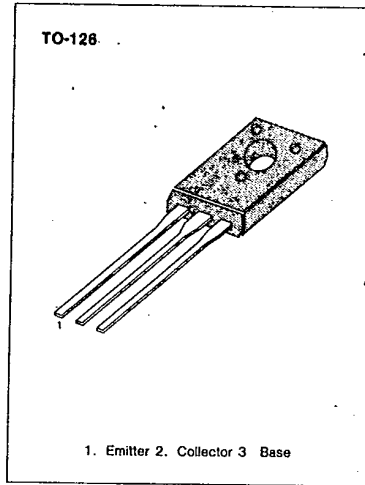


MJE340**NPN EPITAXIAL SILICON TRANSISTOR**

T-33-09

**HIGH COLLECTOR-EMITTER
SUSTAINING VOLTAGE
HIGH VOLTAGE GENERAL PURPOSE
APPLICATIONS
SUITABLE FOR TRANSFORMER**

Complementary to MJE350



3

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	300	V
Collector-Emitter Voltage	V _{CE0}	300	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	500	mA
Collector Dissipation	P _C	20	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-65~150	°C

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

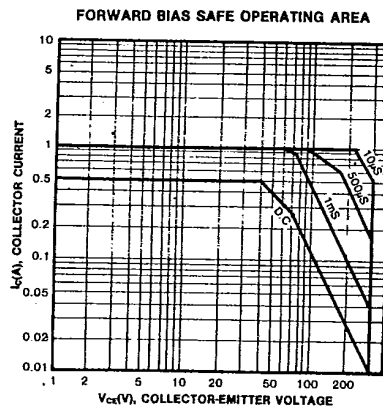
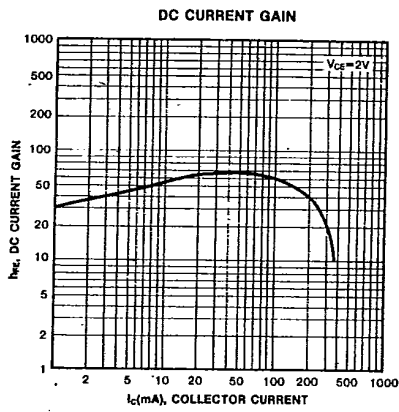
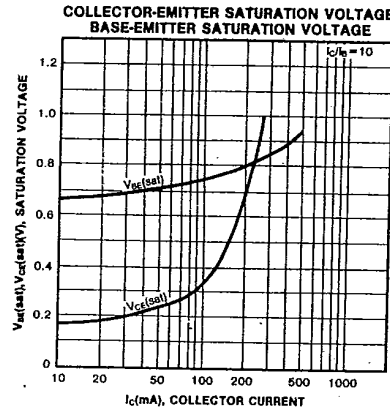
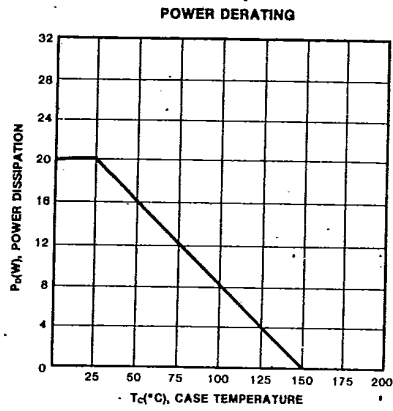
Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Sustaining Voltage	V _{CE0(sus)}	I _C = 1mA, I _B = 0	300		V
Collector Cutoff Current	I _{CB0}	V _{CB} = 300V, I _E = 0		100	μA
Emitter Cutoff Current	I _{EB0}	V _{BE} = 3V, I _C = 0		100	μA
DC Current Gain	h _{FE}	V _{CE} = 10V, I _C = 50mA	30	240	



MJE340

NPN EPITAXIAL SILICON TRANSISTOR

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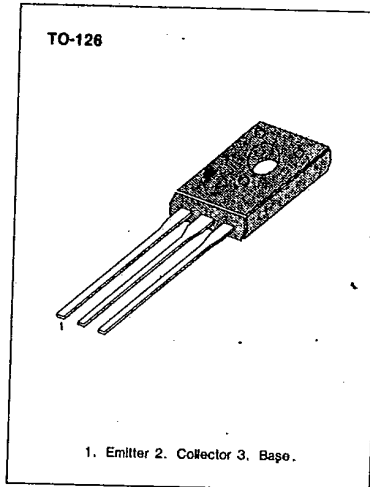
T-33-19

**HIGH COLLECTOR-EMITTER
SUSTAINING VOLTAGE
HIGH VOLTAGE GENERAL PURPOSE
APPLICATIONS
SUITABLE FOR TRANSFORMER**

Complementary to MJE340

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-300	V
Collector-Emitter Voltage	V_{CE0}	-300	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_c	-500	mA
Collector Dissipation	P_c	20	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65~150	$^\circ\text{C}$



3

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CE0(sus)}$	$I_c = -1\text{mA}, I_B = 0$	-300		V
Collector Cutoff Current	I_{CB0}	$V_{CB} = -300\text{V}, I_E = 0$		-100	μA
Emitter Cutoff Current	I_{EB0}	$V_{BE} = -3\text{V}, I_C = 0$		-100	μA
DC Current Gain	h_{FE}	$V_{CE} = -10\text{V}, I_C = -50\text{mA}$	30	240	



MJE350

PNP EPITAXIAL SILICON TRANSISTOR

T-33-19

